



SHANGHAI SUNRISE ELECTRONICS CO., LTD.

IN4148

SILICON EPITAXIAL PLANAR
SWITCHING DIODE

REVERSE VOLTAGE: 75V

FORWARD CURRENT: 150mA

TECHNICAL
SPECIFICATION

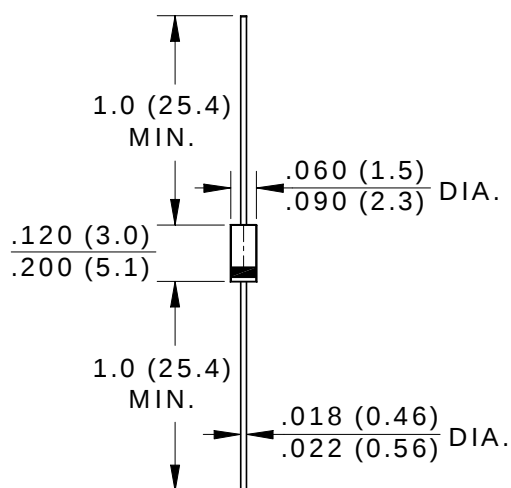
FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:
250°C/10S/9.5mm lead length
at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per
MIL-STD 202E, method 208C
- Case: Glass, hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

DO - 35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE	UNITS
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Forward Current (average)	I_O	150	mA
Repetitive Forward Peak Current	I_{FRM}	300	mA
Forward Voltage ($I_F=10mA$)	V_F	1	V
Reverse Current ($V_R=20V$)	I_{R1}	25	nA
Reverse Current ($V_R=75V$)		5	μA
Reverse Current ($V_R=20V, T_J=100^\circ C$)	I_{R2}	50	μA
Capacitance (note 1)	C_t	4	pF
Reverse Recovery Time (note 2)	I_F	4	nS
Thermal Resistance (junction to ambient) (note 3)	$R_{\theta(ja)}$	0.35	$^\circ C/mW$
Operating Junction and Storage Temperature Range	T_{STG}, T_J	-55 ~ +175	$^\circ C$

Notes:

- 1: $V_R=0V$, $f=1$ MHz
- 2: $I_F=10mA$ to $I_R=1mA$, $V_R=6V$, $R_L=100\Omega$
- 3: Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.

<http://www.sse-diode.com>